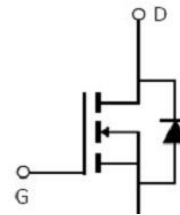


C :

V_{DSS}	150V
$R_{DS(on)}$	9.2m (p.)
I_D	85A


-263 (D2 AK)

D
F B :

Advanced MOSFET process technology
 Special designed for PWM, load switching and
 general purpose applications
 Ultra low on-resistance in high gate charge
 Fast switching and reverse body recovery
 150 operating temperature


D :

Utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance in high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching applications and a wide variety of other applications.

A :

$I_D @ T_C = 25\text{ }^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	85	A
I_{DM}	Pulsed Drain Current	340	
$P_D @ T_C = 25\text{ }^\circ\text{C}$	Power Dissipation	178	W
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

	C			
R _{JC}	Junction-to-case		0.7	/W

E C @T_A=25 unless otherwise specified

					C
V _{(BR)DSS}	Drain-to-Source breakdown voltage	150			V V _{GS} = 0V, I _D = 250 A
R _{DS(on)}	Static Drain-to-Source on-resistance		9.2	12	m V _{GS} =10V, I _D =30A
V _{GS(th)}	Gate threshold voltage	2.5		3.5	V V _{DS} = V _{GS} , I _D =250 A
I _{DSS}	Drain-to-Source leakage current			1	A V _{DS} =150V, V _{GS} = 0V
I _{GSS}	Gate-to-Source forward leakage			100	nA V _{GS} =20V
				-100	V _{GS} = -20V
Q _g	Total gate charge		27		nC I _D = 20A, V _{DS} =75V, V _{GS} = 10V
Q _{gs}	Gate-to-Source charge		8		
Q _{gd}	Gate-to-Drain("Miller") charge		3		
t _{d(on)}	Turn-on delay time		12		ns V _{GS} =10V, R _{GEN} =10 I _D = 20A, V _{DS} =75V
t _r	Rise time		9		
t _{d(off)}	Turn-Off delay time		17		
t _f	Fall time		7		pF V _{GS} = 0V V _{DS} = 25V = 1MH
C _{iss}	Input capacitance		2365		
C _{oss}	Output capacitance		1764		
C _{rss}	Reverse transfer capacitance		113		

-D
C
C

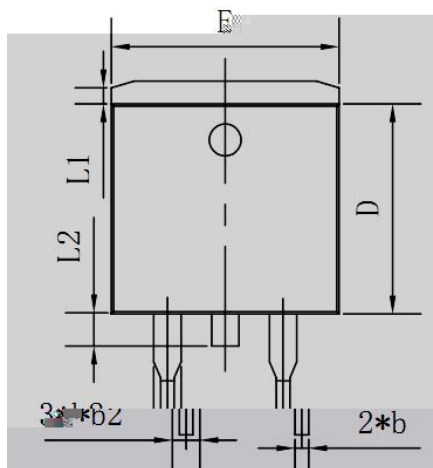
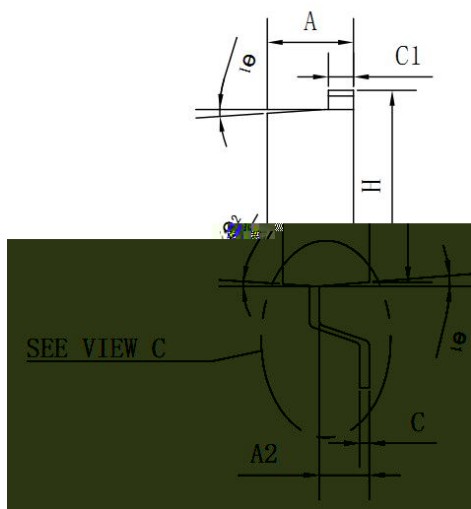
I _S	Continuous Source Current (Body Diode)	85	A	MOSFET symbol showing the integral reverse
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D

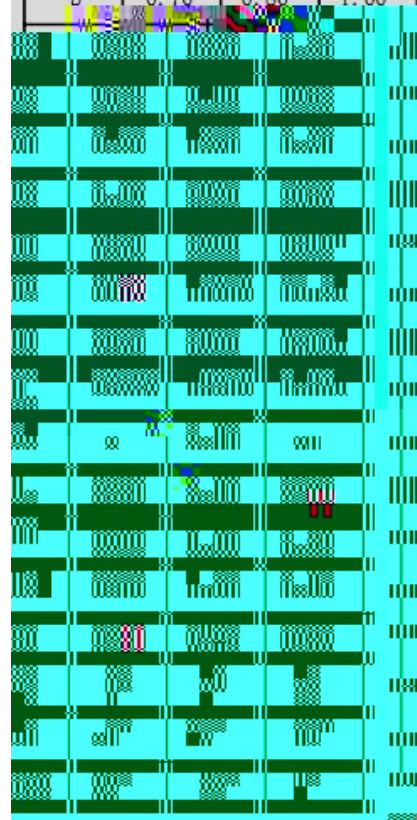
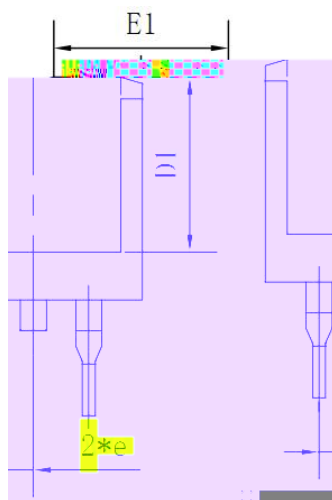
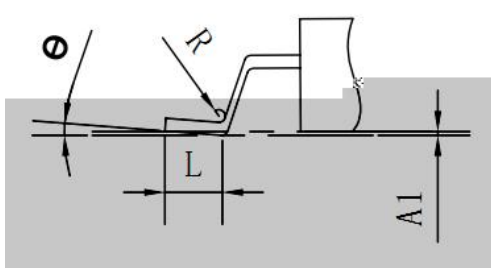
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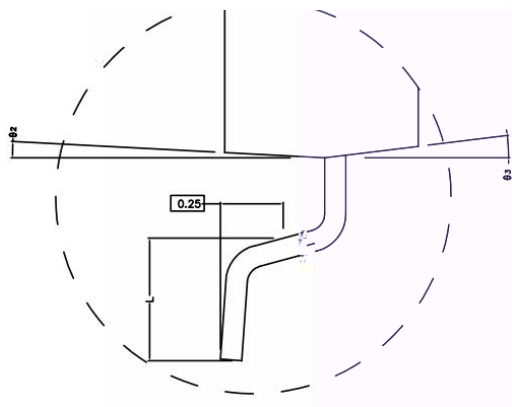
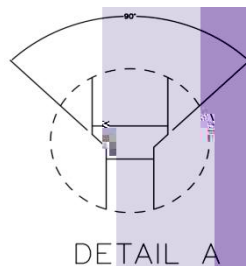
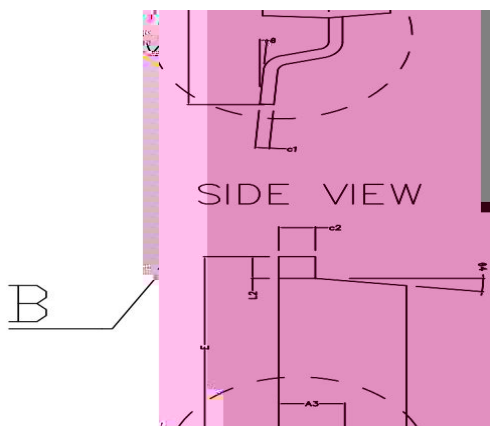
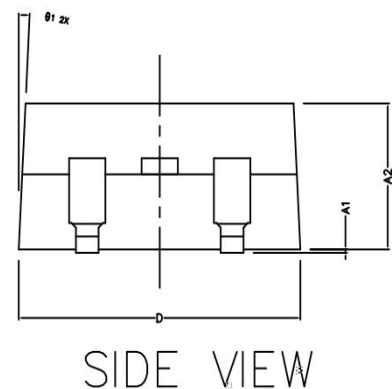
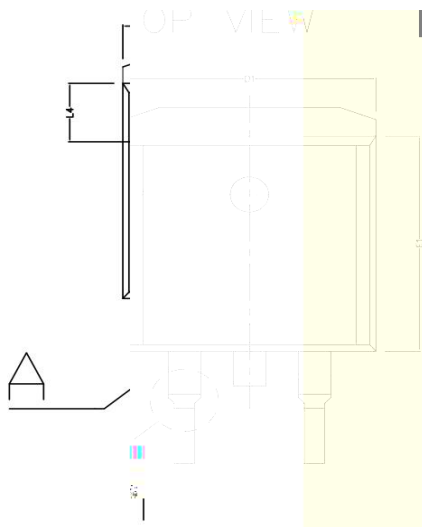
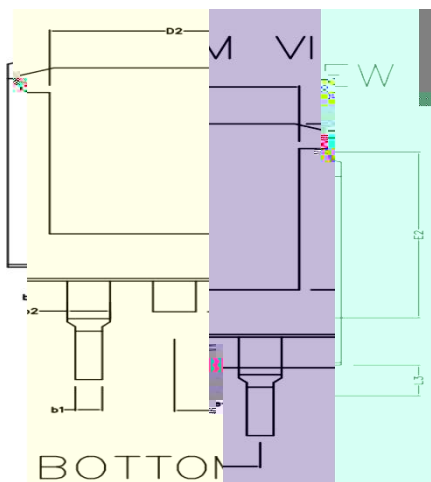
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SYMBOL	MIN	NOM	MAX
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.50
b	0.70	0.80	1.00





	MIN	NORMAL	MAX
A1	0.020		0.200
A2	4.470	4.570	4.67
A3	2.300	2.350	2.40
b1	0.750	-	0.85
b2	1.220	-	1.32
c1	0.500	-	0.5
c2	1.300	-	1.3
D	9.750	9.850	9.9
D1		9.850REF	
D2		7.400REF	
E	14.900	15.100	15.2
E1	9.100	9.200	9.3
E2		8.100REF	
e		2.540REF	
L2	2.100	2.300	2.4
L3	1.025		1.1
L4	1.300	1.500	1.6
L4	2.400		2.60
R1		3° TYP	
R2		5° TYP	
W			
W			
W			
W			

And all other products described or contained herein do not have specific instructions for handling applications
that require a high level of reliability, safety, or performance.

